

Claim Amendments:

1. (Withdrawn)
2. (Withdrawn)
3. (Withdrawn)
4. (Withdrawn)
5. (Withdrawn)
6. (Withdrawn)
7. (Withdrawn)
8. (Withdrawn)
9. (Withdrawn)
10. (Withdrawn)
11. (Withdrawn)
12. (Withdrawn)

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13. (Withdrawn)

14. (Currently Amended) A memory device having an accessible source such that device parameters can be determined, comprising:

a dimple ground into a back-side of a semiconductor substrate of the device;

a trench milled from the bottom portion of the dimple exposing a portion of a vertical trench fill; and

a conductive material connecting the vertical trench fill and a ~~source~~ buried plate of the device.

15. (Currently Amended) The system of claim ~~15~~14, wherein the trench is milled into a portion of the vertical trench fill and the buried plate.

16. (Currently Amended) The system of claim ~~15~~14, wherein the conductive material is a back-side electrode.

17. (Currently Amended) The system of claim ~~15~~14, wherein the conductive material is a layer covering a portion of the back-side of the semiconductor substrate.

18. (Currently Amended) The system of claim ~~15~~14, wherein a macro design of the memory device is substantially similar to a product line macro design.

19. (Currently Amended) The system of claim ~~19~~18, wherein the memory device dimensions are substantially the same as those of the product line macro design.